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#### Details

Product Status	Active
Core Processor	e200z7d
Core Size	32-Bit Dual-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, FlexRay, I <sup>2</sup> C, LINbus, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	-
Program Memory Size	1.5MB (1.5M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	384K x 8
Voltage - Supply (Vcc/Vdd)	1.14V ~ 5.5V
Data Converters	A/D 22x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	257-LFBGA
Supplier Device Package	257-LFBGA (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5674kavmm2r

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### **Pin Assignments**

# 3.2 416-ball TEPBGA Pin Assignments

Figure 6 shows the 416-ball TEPBGA pin assignments in one figure. The same information is shown in Figure 7 through Figure 10.

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	
A	VSS	VDD	RSTOUT	ANA0	ANA4	ANA8	ANA11	ANA15	VDDA_A0	REF- BYPCA1	VRL_A	VRH_A	AN28	AN32	AN36	VDDA_BO	REF- BYPCB1	VRL_B	VRH_B	ANB7	ANB11	ANB14	ANB17	ANB21	ANB23	VSS	A
В	VDDEH1	VSS	VDD	TEST	ANA1	ANA5	ANA10	ANA14	VDDA_A1	VSSA_A1	REF- BYPCA	AN24	AN27	AN29	AN33	VDDA_B1	VSSA_BO	REF- BYPCB	ANB6	ANB8	ANB10	ANB15	ANB18	ANB22	VSS	TCRCLKC	В
С	ETPUA30	ETPUA31	VSS	VDD	ANA2	ANA6	ANA9	ANA13	ANA17	ANA19	ANA21	ANA23	AN26	AN30	AN34	AN37	AN38	ANB0	ANB4	ANB5	ANB12	ANB16	ANB19	VSS	ETPUC0	ETPUC1	С
D	ETPUA27	ETPUA28	ETPUA29	VSS	VDD	ANA3	ANA7	ANA12	ANA16	ANA18	ANA20	ANA22	AN25	AN31	AN35	AN39	ANB1	ANB2	ANB3	ANB9	ANB13	ANB20	VSS	VDDEH7	ETPUC2	ETPUC3	D
E	ETPUA23	ETPUA24	ETPUA25	ETPUA26																			VDDEH7	ETPUC4	ETPUC5	ETPUC6	E
F	ETPUA19	ETPUA20	ETPUA21	ETPUA22					_									_					ETPUC7	ETPUC8	ETPUC9	ETPUC10	F
G	ETPUA15	ETPUA16	ETPUA17	ETPUA18					N		567	4F	416	5-ba	all T	ΈP	BG	A					ETPUC11	ETPUC12	ETPUC13	ETPUC14	G
Н	ETPUA11	ETPUA12	ETPUA14	ETPUA13					(	as vie	eweu	nom	iop	unou	gn m	e pac	каде	*)					ETPUC15	ETPUC16	ETPUC17	ETPUC18	н
J	ETPUA7	ETPUA8	ETPUA9	ETPUA10																			ETPUC19	ETPUC20	ETPUC21	ETPUC22	J
K	ETPUA3	ETPUA4	ETPUA5	ETPUA6						VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS						ETPUC23	ETPUC24	ETPUC25	ETPUC26	к
L	TCRCLKA	ETPUA0	ETPUA1	ETPUA2						VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS						ETPUC27	ETPUC28	ETPUC29	ETPUC30	L
М	VDD33_1	TXDA	RXDA	VSTBY						VSS	VSS	VSS	VSS	VSS	VSS	VSS	VSS						ETPUC31	ETPUB15	ETPUB14	VDDEH7	М
N	RXDB	BOOT-	WKPCFG	VDD						VDDE2	VSS	VSS	VSS	VSS	VSS	VSS	VSS						VDDEH6	ETPUB11	ETPUB12	ETPUB13	S N
P	TXDB	PLLCFG1	PLLCFG2	VDDEH1						VDDE2	VDDE2	VSS	VSS	VSS	VSS	VSS	VSS						ETPUB7	ETPUB8	ETPUB9	ETPUB10	P
R	JCOMP	RESET	PLLCFG0	RDY						VDDE2	VDDE2	VSS	VSS	VSS	VSS	VSS	VSS						ETPUB3	ETPUB4	ETPUB5	ETPUB6	R
T	VDDE2	мско	MSEO1	EVTI						VDDE2	VDDE2	VDDE2	VSS	VSS	VSS	VSS	VSS						TCRCLKB	ETPUB0	ETPUB1	ETPUB2	т
U	EVTO	MSEO0	MDO0	MD01						VDDE2	VDDE2	VDDE2	VSS	VSS	VSS	VSS	VSS						ETPUB19	ETPUB18	ETPUB17	ETPUB16	5 U
v	MDO2	MD03	MDO4	MDO5																			FTPUB26	FTPUB22	FTPUB21	FTPUB20	v
w	MDOS	MD07	MD08	VDDF2																			REGSEL	ETPUB25	FTPUR24	ETPLIB23	w
v	MDO9	MD010	MD011	MD015																			FTPI IR29	ETPUB28	ETPUR27	REGCTI	v
۰	MDO12	MD013		VDD33_2																				ETPUB30	VDDREG	VSSSVN	
^//	TDO	тск	TMS	VDD35_2																			VDD 00_0	ETDUR31	VSSEI	EYTAL	
AD	VDDE2	TDI	VDD	VCC		DCCA4	DCCAD	DCCD4	DCCD4			ממע	EMIOCO	EMIORIA		EMIOSOO	EMIOSOZ	EMIOSO4	CNDVD	CNDVD		DCCC4	VCC			VTAL	AD
AC			VDD	FR A	FR B	POSAT	PUSAZ	PC5B4	PCSBI	VUUEH3			EMIOS	EMIOS14	EMIOSIS	EMIOS22	EMIOSZI	EMIOSSI	CNRAB	CINKAD		PUSUI	V00	VDD		VEROVA	
AD	ENGCLK	VDD	FR A	TX FR B	TX	PCSA5	SOUTA	SCKA	PCSB0	PCSB3	EMIOS2	EMIOSS	EMIO59	EMIOS15	EMIOS19	EMIO523	EMIO526	EMIO530	CNIXB	CNIXD	SCKC	RADC	PC5C3	V55	VDD	VUUSIN	AD
AE	VDD	VSS	RX FR A	RX FR B	PCSA4	PCSAO	PCSA3	SCKB	SINB	EMIOS0	EMIOS3	EMIOS6	EMIOS10	EMIOS13	EMIOS17	EMIOS21	EMIOS25	EMIOS29	UNRXA	CNRXC	PCSCU	SINC	PCSC2	PCSC5	VSS	טטע	AE
AF	VSS	VDDE2	TX_EN	TX_EN	VDDEH3	PCSB5	SINA 7	PCSB2	SOUTB	EMIOS1	EMIOS4	EMIOS7	EMIOS11	EMIOS12	EMIOS16	EMIOS20	17 EMIOS24	EMIOS28		20	SOUTC 21	VDDEH4	TXDC 23	PCSC4	VDDEH5	26 VSS	AF
		2	0	Ŧ	0	U	Fig	gure	. 6. N	ИРС	5674	4F 4	16-b	all 1	<b>EPE</b>	3GA	(ful	l dia	igra	<b>m</b> )	21	~~~	20	27	20	20	

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- <sup>1</sup> Functional operating conditions are given in the DC electrical specifications. Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the listed maxima may affect device reliability or cause permanent damage to the device.
- <sup>2</sup> 2.0 V for 10 hours cumulative time, 1.2 V +10% for time remaining.
- $^3$  6.4 V for 10 hours cumulative time, 5.0 V +10% for time remaining.
- <sup>4</sup> Voltage overshoots during a high-to-low or low-to-high transition must not exceed 10 seconds per instance.
- $^{5}$  5.3 V for 10 hours cumulative time, 3.3 V +10% for time remaining.
- <sup>6</sup> MPC5674F has two analog power supply pins on the pinout: VDDA\_A and VDDA\_B.
- <sup>7</sup> MPC5674F has two analog ground supply pins on the pinout: VSSA\_A and VSSA\_B.
- <sup>8</sup> MPC5674F has two analog low reference voltage pins on the pinout: VRL\_A and VRL\_B.
- <sup>9</sup> MPC5674F has two analog high reference voltage pins on the pinout: VRH\_A and VRH\_B.
- <sup>10</sup> Total injection current for all pins must not exceed 25 mA at maximum operating voltage.
- <sup>11</sup> Injection current of ±5 mA allowed for limited duration for analog (ADC) pads and digital 5 V pads. The maximum accumulated time at this current shall be 60 hours. This includes an assumption of a 5.25 V maximum analog or V<sub>DDEH</sub> supply when under this stress condition.
- <sup>12</sup> Total injection current for all analog input pins must not exceed 15 mA.
- <sup>13</sup> Lifetime operation at these specification limits is not guaranteed.
- <sup>14</sup> Solder profile per CDF-AEC-Q100.
- <sup>15</sup> Moisture sensitivity per JEDEC test method A112.

# 4.2 Thermal Characteristics

### Table 4. Thermal Characteristics, 416-pin TEPBGA Package<sup>1</sup>

Characteristic	Symbol	Value	Unit
Junction to Ambient <sup>2,3</sup> Natural Convection (Single layer board)	R <sub>θJA</sub>	24	°C/W
Junction to Ambient <sup>2,4</sup> Natural Convection (Four layer board 2s2p)	R <sub>θJA</sub>	18	°C/W
Junction to Ambient (@200 ft./min., Single layer board)	R <sub>θJMA</sub>	19	°C/W
Junction to Ambient (@200 ft./min., Four layer board 2s2p)	R <sub>θJMA</sub>	14	°C/W
Junction to Board <sup>5</sup>	R <sub>θJB</sub>	9	°C/W
Junction to Case <sup>6</sup>	R <sub>θJC</sub>	6	°C/W
Junction to Package Top <sup>7</sup> Natural Convection	$\Psi_{JT}$	2	°C/W

<sup>1</sup> Thermal characteristics are targets based on simulation that are subject to change per device characterization. This data is PRELIMINARY based on similar package used on other devices.

- <sup>2</sup> Junction temperature is a function of on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
- <sup>3</sup> Per JEDEC JESD51-2 with the single layer board horizontal. Board meets JESD51-9 specification.
- <sup>4</sup> Per JEDEC JESD51-6 with the board horizontal.
- <sup>5</sup> Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- <sup>6</sup> Indicates the average thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1) with the cold plate temperature used for the case temperature.
- <sup>7</sup> Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.



- <sup>6</sup> Indicates the average thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1) with the cold plate temperature used for the case temperature.
- <sup>7</sup> Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.

## 4.2.1 General Notes for Specifications at Maximum Junction Temperature

An estimation of the chip junction temperature, T<sub>J</sub>, can be obtained from the equation:

$$T_{J} = T_{A} + (R_{\theta JA} * P_{D})$$
 Eqn. 1

where:

 $T_A$  = ambient temperature for the package (<sup>o</sup>C)

 $R_{\theta IA}$  = junction to ambient thermal resistance (°C/W)

 $P_D$  = power dissipation in the package (W)

The junction to ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. Unfortunately, there are two values in common usage: the value determined on a single layer board and the value obtained on a board with two planes. For packages such as the TEPBGA, these values can be different by a factor of two. Which value is closer to the application depends on the power dissipated by other components on the board. The value obtained on a single layer board is appropriate for the tightly packed printed circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated.

When a heat sink is used, the thermal resistance is expressed as the sum of a junction to case thermal resistance and a case to ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$
 Eqn. 2

where:

 $R_{\theta IA}$  = junction to ambient thermal resistance (<sup>o</sup>C/W)

 $R_{\Theta IC}$  = junction to case thermal resistance (°C/W)

 $R_{\theta CA}$  = case to ambient thermal resistance (°C/W)

 $R_{\theta JC}$  is device related and cannot be influenced by the user. The user controls the thermal environment to change the case to ambient thermal resistance,  $R_{\theta CA}$ . For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device.

To determine the junction temperature of the device in the application when heat sinks are not used, the Thermal Characterization Parameter ( $\Psi_{JT}$ ) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$
 Eqn. 3

where:

 $T_T$  = thermocouple temperature on top of the package (<sup>o</sup>C)

 $\Psi_{JT}$  = thermal characterization parameter (<sup>o</sup>C/W)

 $P_D$  = power dissipation in the package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the



package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm. of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

### **References:**

Semiconductor Equipment and Materials International 3081 Zanker Road San Jose, CA 95134 (408) 943-6900

MIL-SPEC and EIA/JESD (JEDEC) specifications are available from Global Engineering Documents at 800-854-7179 or 303-397-7956.

JEDEC specifications are available on the WEB at http://www.jedec.org.

- C.E. Triplett and B. Joiner, "An Experimental Characterization of a 272 PBGA Within an Automotive Engine Controller Module," Proceedings of SemiTherm, San Diego, 1998, pp. 47-54.
- G. Kromann, S. Shidore, and S. Addison, "Thermal Modeling of a PBGA for Air-Cooled Applications," Electronic Packaging and Production, pp. 53-58, March 1998.
- B. Joiner and V. Adams, "Measurement and Simulation of Junction to Board Thermal Resistance and Its Application in Thermal Modeling," Proceedings of SemiTherm, San Diego, 1999, pp. 212-220.

# 4.3 EMI (Electromagnetic Interference) Characteristics

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions, go to www.freescale.com and perform a keyword search for "radiated emissions." The following tables list the values of the device's radiated emissions operating behaviors.

Symbol	Description Conditions		f <sub>osc</sub> f <sub>sys</sub>	Frequency band (MHz)	Level (max.)	Unit	Notes
V <sub>RE_TEM</sub>	Radiated emissions,	$V_{DD} = 1.2 V$	40 MHz crystal	0.15–50	26	dBμV	1
	magnetic field	V <sub>DDE</sub> = 3.3 V V <sub>DDEH</sub> = 5 V	264 MHZ (f <sub>FBL CAL</sub> = 66	50–150	30		
	Ũ	T <sub>A</sub> = 25 °C 416 BGA EBI off	MHz)	150–500	34		
				500–1000	30		
		CLK on FM off		IEC and SAE level	l <sup>2</sup>	—	1, 3
V <sub>RE_TEM</sub>	Radiated emissions,	$V_{DD} = 1.2 V$	40 MHz crystal	0.15–50	24	dBμV	1
	magnetic field	V <sub>DDE</sub> = 3.3 V V <sub>DDEH</sub> = 5 V	264 MHZ (f <sub>EBL CAL</sub> = 66	50–150	25		
		$T_A = 25 \text{ °C}$	MHz)	150–500	25		
		EBI off CLK off FM on <sup>4</sup>		500–1000	21		
				IEC and SAE level	K <sup>5</sup>	_	1,3

### Table 7. EMC Radiated Emissions Operating Behaviors: 416 BGA

<sup>1</sup> Determined according to IEC Standard 61967-2, Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method, and SAE Standard J1752-3, Measurement of Radiated Emissions from Integrated Circuits—TEM/Wideband TEM (GTEM) Cell Method.

<sup>2</sup> I = 36 dB $\mu$ V

<sup>3</sup> Specified according to Annex D of IEC Standard 61967-2, Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method, and Appendix D of SAE Standard J1752-3, Measurement of Radiated Emissions from Integrated Circuits—TEM/Wideband TEM (GTEM) Cell Method.



- <sup>4</sup> "FM on" = FM depth of  $\pm 2\%$
- <sup>5</sup> K = 30 dB $\mu$ V

Symbol Description Co		Conditions	f <sub>osc</sub> f <sub>sys</sub>	Frequency band (MHz)	Level (max.)	Unit	Notes
V <sub>RE_TEM</sub>	Radiated emissions,	V <sub>DD</sub> = 1.2 V	40 MHz crystal	0.15–50	40	dBμV	1
	electric field and magnetic field	V <sub>DDE</sub> = 3.3 V V <sub>DDEH</sub> = 5 V	264 MHz (f <sub>FBL CAL</sub> = 66	50–150	48		
		$T_A = 25 \text{ °C}$	MHz)	150–500	48		
		EBI on		500–1000	47		
		CLK on FM off		IEC and SAE level	G <sup>2</sup>	—	1, 3
V <sub>RE_TEM</sub>	Radiated emissions,	$V_{DD} = 1.2 V$	40 MHz crystal	0.15–50	40	dBμV	1
	magnetic field	V <sub>DDE</sub> = 3.3 V V <sub>DDEH</sub> = 5 V	264 MHz (feren con = 66	50–150	44		
		$T_A = 25 \text{ °C}$	MHz)	150–500	41		
		EBI on		500–1000	36		
		CLK on FM on <sup>4</sup>		IEC and SAE level	G <sup>2</sup>	—	1, 3

### Table 8. EMC Radiated Emissions Operating Behaviors: 516 BGA

<sup>1</sup> Determined according to IEC Standard 61967-2, Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method, and SAE Standard J1752-3, Measurement of Radiated Emissions from Integrated Circuits—TEM/Wideband TEM (GTEM) Cell Method.

<sup>2</sup> G = 48 dB $\mu$ V

<sup>3</sup> Specified according to Annex D of IEC Standard 61967-2, Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method, and Appendix D of SAE Standard J1752-3, Measurement of Radiated Emissions from Integrated Circuits—TEM/Wideband TEM (GTEM) Cell Method.

<sup>4</sup> "FM on" = FM depth of  $\pm 2\%$ 

# 4.4 ESD Characteristics

### Table 9. ESD Ratings<sup>1,2</sup>

Spec	Characteristic	Symbol	Value	Unit
1	ESD for Human Body Model (HBM)	V <sub>HBM</sub>	2000	V
2	ESD for Charged Device Model (CDM)	V <sub>CDM</sub>	750 (corners) 500 (other)	V

<sup>1</sup> All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.

<sup>2</sup> A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

# 4.5 PMC/POR/LVI Electrical Specifications

Note: For ADC internal resource measurements, see Table 21 in Section 4.9.1, "ADC Internal Resource Measurements."

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Spec	Characteristic	Symbol	Min	Max	Unit
9	Offset Error without Calibration	OFFNC	04	100 <sup>4</sup>	LSB
10	Offset Error with Calibration	OFFWC	-4 <sup>4</sup>	4 <sup>4</sup>	LSB
11	Full Scale Gain Error without Calibration	GAINNC	-120 <sup>4</sup>	04	LSB
12	Full Scale Gain Error with Calibration	GAINWC	-4 <sup>4,6</sup>	4 <sup>4,6</sup>	LSB
13	Non-Disruptive Input Injection Current 7, 8, 9, 10	I <sub>INJ</sub>	-3	3	mA
14	Incremental Error due to injection current <sup>11, 12</sup>	E <sub>INJ</sub>	-4 <sup>4</sup>	4 <sup>4</sup>	Counts
15	TUE value at 8 MHz <sup>13, 14</sup> (with calibration)	TUE8	-4 <sup>4,6</sup>	4 <sup>4,6</sup>	Counts
16	TUE value at 16 MHz <sup>13, 14</sup> (with calibration)	TUE16	-8	8	Counts
17	Maximum differential voltage <sup>15</sup> (DANx+ - DANx-) or (DANx DANx+) PREGAIN set to 1X setting PREGAIN set to 2X setting PREGAIN set to 4X setting	DIFF <sub>max</sub> DIFF <sub>max2</sub> DIFF <sub>max4</sub>	 	(V <sub>RH</sub> – V <sub>RL</sub> )/2 (V <sub>RH</sub> – V <sub>RL</sub> )/4 (V <sub>RH</sub> - V <sub>RL</sub> )/8	V V V
18	Differential input Common mode voltage <sup>15</sup> (DANx- + DANx+)/2	DIFF <sub>cmv</sub>	(V <sub>RH</sub> – V <sub>RL</sub> )/2 – 5%	(V <sub>RH</sub> – V <sub>RL</sub> )/2 + 5%	V

### Table 20. eQADC Conversion Specifications (Operating) (continued)

<sup>1</sup> Stop mode recovery time is the time from the setting of either of the enable bits in the ADC Control Register to the time that the ADC is ready to perform conversions. Delay from power up to full accuracy = 8 ms.

<sup>2</sup> At  $V_{RH} - V_{RL} = 5.12$  V, one count = 1.25 mV without using pregain.

<sup>3</sup> INL and DNL are tested from  $V_{RL}$  + 50 LSB to  $V_{RH}$  – 50 LSB. The eQADC is guaranteed to be monotonic at 10 bit accuracy (12 bit resolution selected).

<sup>4</sup> New design target. Actual specification will change following characterization. Margin for manufacturing has not been fully included.

 $^5\,$  At V\_{RH} - V\_{RL} = 5.12 V, one LSB = 1.25 mV.

- <sup>6</sup> The value is valid at 8 MHz, it is ±8 counts at 16 Mhz.
- <sup>7</sup> Below disruptive current conditions, the channel being stressed has conversion values of \$3FF for analog inputs greater than V<sub>RH</sub> and \$000 for values less than V<sub>RL</sub>. Other channels are not affected by non-disruptive conditions.
- <sup>8</sup> Exceeding limit may cause conversion error on stressed channels and on unstressed channels. Transitions within the limit do not affect device reliability or cause permanent damage.
- <sup>9</sup> Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values using  $V_{POSCLAMP} = V_{DDA} + 0.5$  V and  $V_{NEGCLAMP} = -0.3$  V, then use the larger of the calculated values.
- <sup>10</sup> Condition applies to two adjacent pins at injection limits.
- <sup>11</sup> Performance expected with production silicon.
- <sup>12</sup> All channels have same 10 k $\Omega$  < Rs < 100 k $\Omega$  Channel under test has Rs = 10 k $\Omega$ ,  $I_{INJ}=I_{INJMAX}$ ,  $I_{INJMIN}$ .
- <sup>13</sup> The TUE specification is always less than the sum of the INL, DNL, offset, and gain errors due to cancelling errors.

<sup>14</sup> TUE does not apply to differential conversions.

<sup>15</sup> Voltages between VRL and VRH will not cause damage to the pins. However, they may not be converted accurately if the differential voltage is above the maximum differential voltage. In addition, conversion errors may occur if the common mode voltage of the differential signal violates the Differential Input common mode voltage specification.



# 4.11.2 Pad AC Specifications

Spec	Pad	SRC/DSC	Out Delay <sup>2,4</sup> L $\rightarrow$ H/H $\rightarrow$ L (ns)	Rise/Fall <sup>3,4</sup> (ns)	Load Drive (pF)							
1	Medium <sup>5</sup>	00	152/165	70/74	50							
2			205/220	96/96	200							
3		01	28/34	12/15	50							
4			52/59	28/31	200							
5		11	12/12	5.3/5.9	50							
6			32/32	22/22	200							
7	Fast <sup>6</sup>	00			10							
8		01	2.5	1.2	20							
9		10	2.0	1.2	30							
10		11			50							
11	Fast with Slew Rate	00	40/40	16/16	50							
12			50/50	21/21	200							
13		01	13/13	5/5	50							
14			19/19	8/8	200							
15		10	8/8	2.4/2.4	50							
16			12/12	5/5	200							
17		11	5/5	1.1/1/1	50							
18			8/8	2.6	2.6							
19	Pull Up/Down (3.6 V max)	—	—	7500	50							
20	Pull Up/Down (5.25 V max)	—	6000	5000/5000	50							

### Table 31. Pad AC Specifications $(V_{DDEH} = 5.0 \text{ V}, V_{DDE} = 3.3 \text{ V})^1$

<sup>1</sup> These are worst case values that are estimated from simulation and not tested. The values in the table are simulated at  $V_{DD} = 1.02$  V to 1.32 V,  $V_{DDE} = 3.0$  V to 3.6 V,  $V_{DDEH} = 4.75$  V to 5.25 V,  $V_{DD33}$  and  $V_{DDSYN} = 3.0$  V to 3.6 V,  $T_A = T_L$  to  $T_H$ .

 $^2$  This parameter is supplied for reference and is not guaranteed by design and not tested.

<sup>3</sup> This parameter is guaranteed by characterization before qualification rather than 100% tested.

<sup>4</sup> Delay and rise/fall are measured to 20% or 80% of the respective signal.

<sup>5</sup> Out delay is shown in Figure 17. Add a maximum of one system clock to the output delay for delay with respect to system clock.

<sup>6</sup> Out delay is shown in Figure 17. Add a maximum of one system clock to the output delay for delay with respect to system clock.

<sup>1</sup> JTAG timing specified at  $V_{DD}$  = 1.08 V to 1.32 V,  $V_{DDE}$  = 3.0 V to 3.6 V,  $V_{DD33}$  and  $V_{DDSYN}$  = 3.0 V to 3.6 V,  $T_A$  =  $T_L$  to  $T_H$ , and  $C_L$  = 30 pF with DSC = 0b10, SRC = 0b00. These specifications apply to JTAG boundary scan only. See Table 35 for functional specifications.



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Figure 22. JTAG Test Access Port Timing



Spec	Characteristic	Symbol	Peripheral Bus	s Freq: 132 MHz	Unit
Spec	Characteristic	Symbol	Min	Мах	Onit
9	Data Setup Time for Inputs Master (MTFE = 0) Slave Master (MTFE = 1, CPHA = $0$ ) <sup>8</sup> Master (MTFE = 1, CPHA = 1)	t <sub>SUI</sub>	20 4 6 20		ns ns ns ns
10	Data Hold Time for Inputs Master (MTFE = 0) Slave Master (MTFE = 1, CPHA = $0$ ) <sup>8</sup> Master (MTFE = 1, CPHA = 1)	t <sub>HI</sub>	-3 7 12 -3		ns ns ns ns
11	Data Valid (after SCK edge) Master (MTFE = 0) Slave Master (MTFE = 1, CPHA = 0) Master (MTFE = 1, CPHA = 1)	t <sub>SUO</sub>	 	5 25 13 5	ns ns ns ns
12	Data Hold Time for Outputs Master (MTFE = 0) Slave Master (MTFE = 1, CPHA = 0) Master (MTFE = 1, CPHA = 1)	t <sub>HO</sub>	-5 2.5 3 -5		ns ns ns ns

### Table 40. DSPI Timing<sup>1 2</sup> (continued)

<sup>1</sup> DSPI timing specified at  $V_{DD}$  = 1.08 V to 1.32 V,  $V_{DDEH}$  = 3.0 V to 5.5 V,  $V_{DD33}$  and  $V_{DDSYN}$  = 3.0 V to 3.6 V, and  $T_A$  =  $T_L$  to  $T_H$ 

<sup>2</sup> Speed is the nominal maximum frequency of platform clock (f<sub>platf</sub>). Max speed is the maximum speed allowed including frequency modulation (FM). 270 MHz parts allow for 264 Mhz for system core clock (f<sub>svs</sub>) + 2% FM.

<sup>3</sup> The minimum DSPI Cycle Time restricts the baud rate selection for given system clock rate. These numbers are calculated based on two devices communicating over a DSPI link.

<sup>4</sup> The actual minimum SCK cycle time is limited by pad performance.

<sup>5</sup> The maximum value is programmable in DSPI\_CTAR*n*[PSSCK] and DSPI\_CTAR*n*[CSSCK].

<sup>6</sup> The maximum value is programmable in DSPI\_CTAR*n*[PASC] and DSPI\_CTAR*n*[ASC].

<sup>7</sup> For example, external master should start SCK clock not earlier than 3 system clock periods after assertion SS

<sup>8</sup> This number is calculated assuming the SMPL\_PT bitfield in DSPI\_MCR is set to 0b10.

The DSPI in this device can be configured to serialize data to an external device that implements the Microsecond Bus protocol. DSPI pins support 5 V logic levels or Low Voltage Differential Signalling (LVDS) for data and clock signals to improve high speed operation.

Table 41.	DSPI	LVDS	Timing <sup>1,</sup>	2
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Characteristic	Symbol	Min	Max	Unit
LVDS Clock to Data/Chip Select Outputs	t <sub>lvdsdata</sub>	–0.25 × t <sub>SCYC</sub>	+0.25 × t <sub>SCYC</sub>	ns

<sup>1</sup> These are typical values that are estimated from simulation.

<sup>2</sup> See DSPI LVDS Pad related data in Table 17.





Figure 36. DSPI Classic SPI Timing — Slave, CPHA = 0



Figure 37. DSPI Classic SPI Timing — Slave, CPHA = 1







Figure 38. DSPI Modified Transfer Format Timing — Master, CPHA = 0



Figure 39. DSPI Modified Transfer Format Timing — Master, CPHA = 1

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CR <sup>1</sup>	Signal Name <sup>2</sup>	ŝ			ion	'pe <sup>5</sup>	Je <sup>6</sup>	State during	State	Packa	age Loo	cation
GPIO/P	Signal Name <sup>2</sup>	PIA/G	Function <sup>4</sup>	Function Summary	Direct	Pad Ty	Voltaç	RESET <sup>7</sup>	after RESET <sup>8</sup>	324	416	516
143	ETPUA29_PCSC2_	Р	ETPUA29	eTPU A channel	I/O	MH	V <sub>DDEH1</sub>	—/WKPCFG	—/WKPCFG	—	D3	D3
	GPIO143	A1	PCSC2	DSPI C peripheral chip select	0							
		A2	—	—	—							
		G	GPIO143	GPIO	I/O							
144	ETPUA30_PCSC3_	Р	ETPUA30	eTPU A channel	I/O	MH	V <sub>DDEH1</sub>	—/WKPCFG	—/WKPCFG	E4	C1	C1
	GPIO144	A1	PCSC3	DSPI C peripheral chip select	0							
		A2	—	—	—							
		G	GPIO144	GPIO	I/O							
145	ETPUA31_PCSC4_	Р	ETPUA31	eTPU A channel	I/O	MH	V <sub>DDEH1</sub>	—/WKPCFG	—/WKPCFG	D3	C2	C2
	GPIO145	A1	PCSC4	DSPI C peripheral chip select	0							
		A2	—	—	_							
		G	GPIO145	GPIO	I/O							
		•		eTPU_B			1					
146	TCRCLKB_IRQ6_	Р	TCRCLKB	eTPU B TCR clock	I	MH	V <sub>DDEH6</sub>	—/Up	—/Up	P19	T23	V25
	GPIO146	A1	IRQ6	External interrupt request	I							
		A2	—	_	_							
		G	GPIO146	GPIO	I/O							
147	ETPUB0_ETPUB16_	Р	ETPUB0	eTPU B channel	I/O	MH	V <sub>DDEH6</sub>	—/WKPCFG	—/WKPCFG	N19	T24	V26
	GPIO147	A1	ETPUB16	eTPU B channel (output only)	0							
		A2	—	-	—							
		G	GPIO147	GPIO	I/O							
148	ETPUB1_ETPUB17_	Р	ETPUB1	eTPU B channel	I/O	MH	V <sub>DDEH6</sub>	—/WKPCFG	—/WKPCFG	R19	T25	U22
	GPIO148	A1	ETPUB17	eTPU B channel (output only)	0							
		A2	—	_	_							
		G	GPIO148	GPIO	I/O							

CR <sup>1</sup>		33			ion	'pe <sup>5</sup>	Je <sup>6</sup>	State during	State	Packa	age Loo	cation
GPIO/P	Signal Name <sup>2</sup>	P/A/0	Function <sup>4</sup>	Function Summary	Direct	Pad Ty	Voltaç	RESET <sup>7</sup>	after RESET <sup>8</sup>	324	416	516
200	EMIOS21_ETPUB5_	Ρ	EMIOS21	eMIOS channel	I/O	MH	V <sub>DDEH4</sub>	—/WKPCFG	—/WKPCFG	AA14	AE16	AE17
	GPIO200	A1	ETPUB5	eTPU B channel	0							
		A2	—	-	_							
		G	GPIO200	GPIO	I/O							
201	EMIOS22_ETPUB6_	Ρ	EMIOS22	eMIOS channel	I/O	MH	V <sub>DDEH4</sub>	—/WKPCFG	—/WKPCFG	W13	AC16	AC16
	GPIO201	A1	ETPUB6	eTPU B channel	0							
		A2	—	-	_							
		G	GPIO201	GPIO	I/O							
202	EMIOS23_ETPUB7_	Ρ	EMIOS23	eMIOS channel	I/O	MH	V <sub>DDEH4</sub>	—/WKPCFG	—/WKPCFG	Y15	AD16	AA16
	GPIO202	A1	ETPUB7	eTPU B channel	0							
		A2	—	-	_							
		G	GPIO202	GPIO	I/O							
203	EMIOS24_PCSB0_	Ρ	EMIOS24	eMIOS channel	I/O	MH	V <sub>DDEH4</sub>	—/WKPCFG	—/WKPCFG	AB16	AF17	AC17
	GPIO203	A1	PCSB0	DSPI B peripheral chip select	I/O							
		A2	—	-	—							
		G	GPIO203	GPIO	I/O							
204	EMIOS25_PCSB1_	Ρ	EMIOS25	eMIOS channel	I/O	MH	V <sub>DDEH4</sub>	—/WKPCFG	—/WKPCFG	AA15	AE17	AF18
	GPIO204	A1	PCSB1	DSPI B peripheral chip select	0							
		A2	—	-	_							
		G	GPIO204	GPIO	I/O							
432	EMIOS26_PCSB2_	Р	EMIOS26	eMIOS channel	I/O	MH	V <sub>DDEH4</sub>	—/WKPCFG	—/WKPCFG	Y16	AD17	AE18
	GPIO432	A1	PCSB2	DSPI B peripheral chip select	0							
		A2	—	-	—							
	(	G	GPIO432	GPIO	I/O							

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CR <sup>1</sup>	2				ion	rpe <sup>5</sup>	Je <sup>6</sup>	State during	State	Packa	ige Loo	ation
GPIO/F	Signal Name <sup>2</sup>	P/A/(	Function <sup>4</sup>	Function Summary	Direct	Pad Ty	Voltaç	RESET <sup>7</sup>	after RESET <sup>8</sup>	324	416	516
—	ANB9	Р	ANB9	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB9	ANB9	C14	D20	A21
-	ANB10	Ρ	ANB10	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB10	ANB10	C13	B21	B21
—	ANB11	Ρ	ANB11	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB11	ANB11	C15	A21	C21
—	ANB12	Ρ	ANB12	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB12	ANB12	C16	C21	A22
—	ANB13	Ρ	ANB13	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB13	ANB13	D14	D21	B22
—	ANB14	Ρ	ANB14	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB14	ANB14	C17	A22	D20
—	ANB15	Ρ	ANB15	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB15	ANB15	D15	B22	C22
—	ANB16	Ρ	ANB16	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB16	ANB16	C18	C22	D21
—	ANB17	Ρ	ANB17	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB17	ANB17	D16	A23	D22
—	ANB18	Ρ	ANB18	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB18	ANB18	D17	B23	A23
—	ANB19	Ρ	ANB19	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB19	ANB19	B19	C23	B23
—	ANB20	Ρ	ANB20	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB20	ANB20	C19	D22	C23
—	ANB21	Ρ	ANB21	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB21	ANB21	D18	A24	A24
—	ANB22	Ρ	ANB22	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB22	ANB22	A21	B24	B24
—	ANB23	Ρ	ANB23	eQADC B analog input	I	AE	V <sub>DDA_B0</sub>	ANB23	ANB23	B20	A25	E20
—	VRH_A	Ρ	VRH_A	ADC A Voltage reference high	Ι	VDDINT	V <sub>RH_A</sub>	VRH_A	VRH_A	A10	A12	A12
—	VRL_A	Ρ	VRL_A	ADC A Voltage reference low	Ι	VSSINT	V <sub>RL_A</sub>	VRL_A	VRL_A	A11	A11	A11
—	VRH_B	Ρ	VRH_B	ADC B Voltage reference high	I	VDDINT	V <sub>RH_B</sub>	VRH_B	VRH_B	A16	A19	A19
—	VRL_B	Ρ	VRL_B	ADC B Voltage reference low	Ι	VSSINT	V <sub>RL_B</sub>	VRL_B	VRL_B	A15	A18	A18
—	REFBYPCB	Ρ	REFBYPCB	ADC B Reference bypass capacitor	Ι	AE	V <sub>DDA_B0</sub>	REFBYPCB	REFBYPCB	B12	B18	B18
—	REFBYPCA	Ρ	REFBYPCA	ADC A Reference bypass capacitor	I	AE	V <sub>DDA_A1</sub>	REFBYPCA	REFBYPCA	B11	B11	B11
—	VDDA_A0	Ρ	VDDA_A	Internal logic supply input	I	VDDE	V <sub>DDA_A0</sub>	VDDA_A0	VDDA_A0	A9	A9	A9
—	VDDA_A1	Ρ	VDDA_A	Internal logic supply input	I	VDDE	V <sub>DDA_A1</sub>	VDDA_A1	VDDA_A1	B9	B9	B9
—	REFBYPCA1	Ρ	REFBYPCA1	ADC A Reference bypass capacitor	I	AE	V <sub>DDA_A1</sub>	REFBYPCA1	REFBYPCA1	A12	A10	A10
—	VSSA_A1	Ρ	VSSA_A	Ground	I	VSSE	V <sub>SSA_A1</sub>	VSSA_A1	VSSA_A1	B10	B10	B10
—	VDDA_B0	Ρ	VDDA_B	Internal logic supply input	I	VDDE	V <sub>DDA_B0</sub>	VDDA_B0	VDDA_B0	A13	A16	A16
—	VDDA_B1	Ρ	VDDA_B	Internal logic supply input	I	VDDE	V <sub>DDA_B1</sub>	VDDA_B1	VDDA_B1	B13	B16	B16

CR <sup>1</sup>		e CD			ion	rpe <sup>5</sup>	Je <sup>6</sup>	State during	State	Packa	age Lo	cation
GPIO/P	Signal Name <sup>2</sup>	P/A/0	Function <sup>4</sup>	Function Summary	Direct	Pad Ty	Voltaç	RESET <sup>7</sup>	after RESET <sup>8</sup>	324	416	516
88	CNRXC_PCSD4_	Ρ	CNRXC	FlexCAN C receive	I	MH	V <sub>DDEH4</sub>	—/Up	—/Up	W17	AE20	AE20
	GPIO88	A1	PCSD4	DSPI D peripheral chip select	0							
		A2	—	—	—							
		G	GPIO88	GPIO	I/O							
246	CNTXD_	Ρ	CNTXD	FlexCAN D transmit	0	MH	V <sub>DDEH4</sub>	—/Up	—/Up	AB21	AD20	AD20
	GPIO246	A1	—	—	—							
		A2	—	—	—							
		G	GPIO246	GPIO	I/O							
247	CNRXD_	Р	CNRXD	FlexCAN D receive	I	MH	V <sub>DDEH4</sub>	—/Up	—/Up	Y19	AC20	AC20
	GPIO247	A1	—	—	—							
		A2	—	—	—							
		G	GPIO247	GPIO	I/O							
		•		eSCI								
89	TXDA_	Ρ	TXDA	eSCI A transmit	0	MH	V <sub>DDEH1</sub>	—/Up	—/Up	—	M2	K2
	GPIO89	A1	—	—	-							
		A2	—	—	-							
		G	GPIO89	GPIO	I/O							
90	RXDA _	Ρ	RXDA	eSCI A receive	I	MH	V <sub>DDEH1</sub>	—/Up	—/Up	_	M3	K3
	GPIO90	A1	—	—	—							
		A2	—	—	—							
		G	GPIO90	GPIO	I							
91	TXDB_PCSD1_	Ρ	TXDB	eSCI B transmit	0	MH	V <sub>DDEH1</sub>	—/Up	—/Up	_	P1	K1
	GPIO91	A1	PCSD1	DSPI D peripheral chip select	0							
		A2	_	<b> </b>	—							
		G	GPIO91	GPIO	I/O							

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CR <sup>1</sup>		33			ion	'pe <sup>5</sup>	je <sup>6</sup>	State during	State	Packa	ige Loo	cation
GPIO/P	Signal Name <sup>2</sup>	P/A/0	Function⁴	Function Summary	Direct	Pad Ty	Voltaç	RESET <sup>7</sup>	after RESET <sup>8</sup>	324	416	516
102	SCKB_	Ρ	SCKB	DSPI B clock	I/O	MH	V <sub>DDEH3</sub>	—/Up	—/Up	Y8	AE8	AC8
	GPI0102	A1	—	—	—							
		A2	—	—	—							
		G	GPIO102	GPIO	I/O							
103	SINB_	Ρ	SINB	DSPI B data input	I	MH	V <sub>DDEH3</sub>	—/Up	—/Up	AA8	AE9	AB9
	GPIO103	A1	—	-	—							
		A2	—	-	—							
		G	GPIO103	GPIO	I/O							
104	SOUTB_	Ρ	SOUTB	DSPI B data output	0	MH	V <sub>DDEH3</sub>	—/Up	—/Up	AB8	AF9	AA10
	GPI0104	A1	—	-	—							
		A2	—	-	—							
		G	GPIO104	GPIO	I/O							
105	PCSB0_PCSD2_	Ρ	PCSB0	DSPI B peripheral chip select	I/O	MH	V <sub>DDEH3</sub>	—/Up	—/Up	Y9	AD9	AF8
	GPI0105	A1	PCSD2	DSPI D peripheral chip select	0							
		A2	—	—	_							
		G	GPIO105	GPIO	I/O							
106	PCSB1_PCSD0_	Ρ	PCSB1	DSPI B peripheral chip select	0	MH	V <sub>DDEH3</sub>	—/Up	—/Up	_	AC9	AE8
	GPI0106	A1	PCSD0	DSPI D peripheral chip select	I/O							
		A2	—	-	—							
		G	GPIO106	GPIO	I/O							
107	PCSB2_SOUTC_	Ρ	PCSB2	DSPI B peripheral chip select	0	MH	V <sub>DDEH3</sub>	—/Up	—/Up	W7	AF8	AD8
	GPIU107	A1	SOUTC	DSPI C data output	0							
		A2	—	-	—							
		G	GPIO107	GPIO	I/O							

CR <sup>1</sup>	2				ion	rpe <sup>5</sup>	ge <sup>6</sup>	State during	State	Packa	ige Loo	cation
GPIO/P	Signal Name <sup>2</sup>	P/A/0	Function <sup>4</sup>	Function Summary	Direct	Pad Ty	Voltaç	RESET <sup>7</sup>	after RESET <sup>8</sup>	324	416	516
108	PCSB3_SINC_	Ρ	PCSB3	DSPI B peripheral chip select	0	MH	V <sub>DDEH3</sub>	—/Up	—/Up		AD10	AC9
	GPIO108	A1	SINC	DSPI C data input	I							
		A2	—	—	-							
		G	GPIO108	GPIO	I/O							
109	PCSB4_SCKC_	Р	PCSB4	DSPI B peripheral chip select	0	MH	V <sub>DDEH3</sub>	—/Up	—/Up		AC8	AF7
	GPIO109	A1	SCKC	DSPI C clock	I/O							
		A2	—	—	-							
		G	GPIO109	GPIO	I/O							
110	PCSB5_PCSC0_	Ρ	PCSB5	DSPI B peripheral chip select	0	MH	V <sub>DDEH3</sub>	—/Up	—/Up	_	AF6	AE6
	GPIO110	A1	PCSC0	DSPI C peripheral chip select	I/O							
		A2	—	—	-							
		G	GPIO110	GPIO	I/O							
235	SCKC_SCK_C_LVDSP_	Р	SCKC	DSPI C clock	I/O	MH+	V <sub>DDEH4</sub>	—/Up	—/Up	AA19	AD21	AD21
	GPI0235	A1	SCK_C_LVDSP	LVDS+ downstream signal positive output clock	0	LVDS						
		A2	—	—	-							
		G	GPIO235	GPIO	I/O							
236	SINC_SCK_C_LVDSM_	Ρ	SINC	DSPI C data input	I	MH+	V <sub>DDEH4</sub>	—/Up	—/Up	AA20	AE22	AE22
	GPIO236	A1	SCK_C_LVDSM	LVDS– downstream signal negative output clock	0	LVDS						
		A2	—	—	-							
		G	GPIO236	GPIO	I/O							
237	SOUTC_SOUT_C_LVDSP_	Ρ	SOUTC	DSPI C data output	0	MH+	V <sub>DDEH4</sub>	—/Up	—/Up	AB18	AF21	AF21
	GPI0237	A1	SOUT_C_LVDSP	LVDS+ downstream signal positive output data	0	LVDS						
		A2	—	—	-							
		G	GPIO237	GPIO	I/O							

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CR <sup>1</sup>	2	33			ion	rpe <sup>5</sup>	ge <sup>6</sup>	State during	State	Packa	age Lo	cation
GPIO/P	Signal Name <sup>2</sup>	P/A/0	Function <sup>4</sup>	Function Summary	Direct	Pad Ty	Voltaç	RESET <sup>7</sup>	after RESET <sup>8</sup>	324	416	516
262	D_ADD15_	Ρ	D_ADD15	EBI address bus	I/O	F	V <sub>DDE8</sub>	—/Up	—/Up	_	_	R4
	GP10262	A1	—	—	-							
		A2	—	-	—							
		G	GPIO262	GPIO	I/O							
263	D_ADD16_D_ADD_DAT16_	Ρ	D_ADD16	EBI address bus	I/O	F	V <sub>DDE8</sub>	—/Up	—/Up	_	—	R5
	GPI0263	A1	D_ADD_DAT16	EBI data only in non-mux mode. Address and data in mux mode.	I/O							
		A2	—	—	-							
		G	GPIO263	GPIO	I/O							
264	D_ADD17_D_ADD_DAT17_	Р	D_ADD17	EBI address bus	I/O	F	V <sub>DDE8</sub>	—/Up	—/Up	—	—	T5
	GPIO264	A1	D_ADD_DAT17	EBI data only in non-mux mode. Address and data in mux mode.	I/O							
		A2	—	-	—							
		G	GPIO264	GPIO	I/O							
265	D_ADD18_D_ADD_DAT18_	Р	D_ADD18	EBI address bus	I/O	F	V <sub>DDE8</sub>	—/Up	—/Up	—	—	T2
	GPI0265	A1	D_ADD_DAT18	EBI data only in non-mux mode. Address and data in mux mode.	I/O							
		A2	—	-	—							
		G	GPIO265	GPIO	I/O							
266	D_ADD19_D_ADD_DAT19_	Р	D_ADD19	EBI address bus	I/O	F	V <sub>DDE8</sub>	—/Up	—/Up	—	—	Т3
	GPIO266	A1	D_ADD_DAT19	EBI data only in non-mux mode. Address and data in mux mode.	I/O							
		A2	—	-	—							
		G	GPIO266	GPIO	I/O							
267	D_ADD20_D_ADD_DAT20_	Р	D_ADD20	EBI address bus	I/O	F	V <sub>DDE8</sub>	—/Up	—/Up	—	—	T4
	GPIO267	A1	D_ADD_DAT20	EBI data only in non-mux mode. Address and data in mux mode.	I/O							
		A2	-	-	-							
		G	GPIO267	GPIO	I/O							

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°CR <sup>1</sup>		с <sub>3</sub>			tion	/pe <sup>5</sup>	ge <sup>6</sup>	State during	State	Packa	age Loo	cation
GPIO/F	Signal Name <sup>2</sup>	P/A/	Function <sup>4</sup>	Function Summary	Direct	Pad T <sub>)</sub>	Volta	RESET <sup>7</sup>	after RESET <sup>8</sup>	324	416	516
77	MDO6_GPIO77	_13	MDO6 <sup>15</sup>	Nexus message data out	0	F	V <sub>DDE2</sub>	O/Low	—/Down	T1	W1	W3
	only available on Rev.2 of the	A1	—	—	-							
	device)	A2	—	—	-							
		G	GPIO77	GPIO	I/O							
78	MDO7_GPIO78	_13	MDO7 <sup>15</sup>	Nexus message data out	0	F	V <sub>DDE2</sub>	O/Low	—/Down	T2	W2	Y1
	only available on Rev.2 of the	A1	—	—	-							
	device)	A2	—	—	-							
		G	GPIO78	GPIO	I/O							
79	MDO8_GPIO79	_13	MDO8 <sup>15</sup>	Nexus message data out	0	F	V <sub>DDE2</sub>	O/Low	—/Down	Т3	W3	W5
	only available on Rev.2 of the	A1	—	—	—							
	device)	A2	—	—	—							
		G	GPIO79	GPIO	I/O							
80	MDO9_GPIO80	_13	MDO9 <sup>15</sup>	Nexus message data out	0	F	V <sub>DDE2</sub>	O/Low	—/Down	U1	Y1	Y2
	only available on Rev.2 of the	A1	—	—	—							
	device)	A2	—	_	—							
		G	GPIO80	GPIO	I/O							
81	MDO10_GPIO81	_13	MDO10 <sup>15</sup>	Nexus message data out	0	F	V <sub>DDE2</sub>	O/Low	—/Down	U2	Y2	Y3
	(GPIO function on this pin is only available on Rev.2 of the	A1	—	_	—							
	device)	A2	—	—	—							
		G	GPIO81	GPIO	I/O							
82	MDO11_GPIO82	_ <sup>13</sup>	MDO11 <sup>15</sup>	Nexus message data out	0	F	V <sub>DDE2</sub>	O/Low	—/Down	U3	Y3	Y4
	only available on Rev.2 of the	A1	—	_								
	device)	A2	—	_	—							
	G	G	GPIO82	GPIO	I/O							



### Table 47. Revision History (continued)

Revision (Date)	Description of changes
8 (Jun-2011)	Removed spec 3 from Table 27 "PFCPR1 Settings vs Frequency of Operation" Updated spec 2a (Untrimmed VRC 1.2V) in Table 11 "PMC Electrical Specifications" to a max value of VDD12OUT + 17%. Updated item 26 (Operating Current VDDA Supply) in table 14 "Electrical Specifications" from 30 mA to 40 mA. Updated Note 11 for Table 14 (Electrical Specifications) to read IOH_F = {16,32,47,77} mA and IOL_F = {24,48,71,115} mA for {00,01,10,11} drive mode with VDDE = 3.0 V.
	<ul> <li>Updated ID 9 in Table 11 (PMC Electrical Specifications) to</li> <li>V<sub>REG</sub> = 4.5 V, max DC output current with a max of 80 mA</li> <li>V<sub>REG</sub> = 4.25 V, max DC output current, crank condition with a max of 40 mA</li> <li>Updated Table 17 (DSPI LVDS Pad Specification) with the following: <ul> <li>Spec 1 typical value updated from 40 MHz to 50 MHz</li> <li>Spec 2 added SRC conditions and associated values:</li> </ul> </li> </ul>
	<ul> <li>SRC=0b00 or SRC=0b11 Min 150 mV Max 400 mV</li> <li>SRC=0b01 Min 90 mV Max 320 mV</li> <li>SRC=0b10 Min 160 mV Max 480 mV</li> <li>Spec 3 <ul> <li>Min value from 1.075 V to 1.06 V</li> </ul> </li> </ul>
	<ul> <li>Max value from 1.325 V to 1.39 V</li> <li>Added Spec 5, 6 and 7</li> </ul>
	<ul> <li>Updated table 17 "DSPI LVDS pad specification" to include Temperature with a min value of -40 C and max of 150 C</li> <li>Updated Spec 5 of Table 18, "FMPLL Electrical Specifications" to &lt; 400 us as the Max vaule.</li> <li>Added the sentence "Violating the VCO min/max range may prevent the system from exiting reset." to the end of Footnote 16 of Table 18, "FMPLL Electrical Specifications"</li> <li>Updated Spec 1 of Table 18, "FMPLL Electrical Specifications", Crystal Reference (PLLCFG2 = 0b1) minimum value from 40 MHz to 16 MHz.</li> <li>Updated Spec 1 of Table 18, "FMPLL Electrical Specifications", External Reference (PLLCFG2 = 0b1) minimum value from 40 MHz to 16 MHz.</li> <li>Updated Spec 1 of Table 18, "FMPLL Electrical Specifications", External Reference (PLLCFG2 = 0b1) minimum value from 40 MHz to 16 MHz.</li> <li>Updated Spec 1 of Table 18, "FMPLL Electrical Specifications", External Reference (PLLCFG2 = 0b1) minimum value from 40 MHz to 16 MHz.</li> <li>Updated Spec 1 of Table 18, "FMPLL Electrical Specifications", External Reference (PLLCFG2 = 0b1) minimum value from 40 MHz to 16 MHz.</li> <li>Updated ID 16 MHz.</li> <li>Updated ID 16 in Table 11, "PMC Electrical Specifications", SMPS regulator clock frequency (after reset) 2.4MHz Max</li> </ul>
	Updated Table 16 "Flash EEPROM Module Life", spec 3, 'Blocks with 10,001–100,000 P/E cycles' to 5 Years.
	Added Typ column to Table 25, "Flash Program and Erase Specifications"
	Updated Table 3, "Absolute Maximum Ratings" with the following: - Spec 1, '1.2 V Core Supply Voltage', to a Max of 2.0 V - Spec 3, 'Clock Synthesizer Voltage', to a Max of 5.3 V - Spec 4, 'I/O Supply Voltage' to a Max of 5.3 V - Spec 5, 'Analog Supply Voltage' to a Max of 5.3 V - Note 2 to read, "2.0 V for 10 hours cumulative time, 1.32 V +10% for time remaining." - Note 3, " 5.0 V + 10%" to " 5.25 V + 10 %" - Note 5, " 3.3 V + 10%" to " 3.60 V + 10 %"
	Updated Spec 2 (ESD for Charged Device Model (CDM)) of Table 9, "ESD Ratings", to 500 V
	Updated Table 27, "PFCPR1 Settings vs. Frequency of Operation", Spec 3, APC = RWSC column to 0b100.
	Updated Spec 26, "Operating Current 5.0 V Supplies @ f <sub>sys</sub> = 264 MHz" for I <sub>DDA</sub> to 50 mA, in Table 14, "DC electrical specifications".